Ordering number : EN3235A

2SC4482

Bipolar Transistor
20V, 5A, Low V_{CE}(sat), NPN Single NMP

ON Semiconductor®
http://onsemi.com

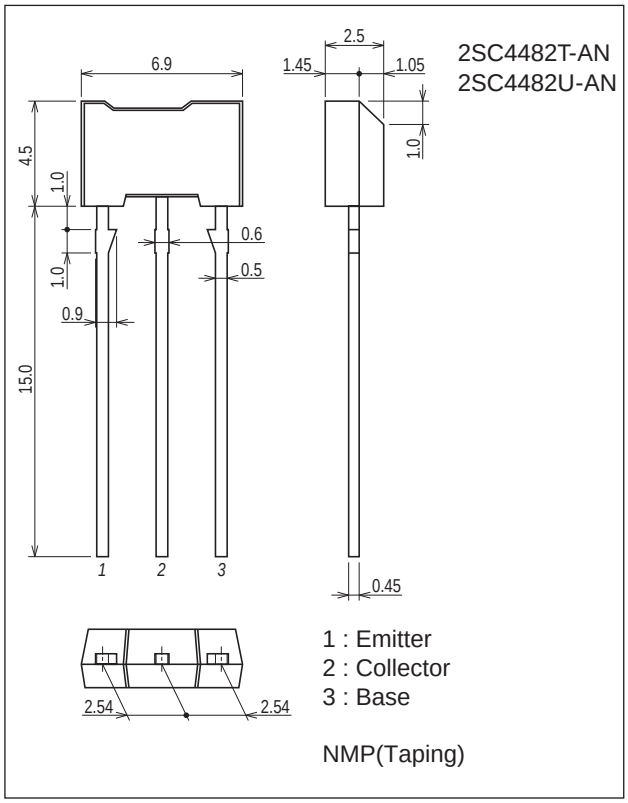
Features
- Low saturation voltage
- Large current capacity
- High-speed switching

Specifications
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		60	V
Collector-to-Emitter Voltage	V_{CEO}		20	V
Emitter-to-Base Voltage	V_{EBO}		6	V
Collector Current	I_C		5	A
Collector Current (Pulse)	I_{CP}		8	A
Collector Dissipation	P_C		1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

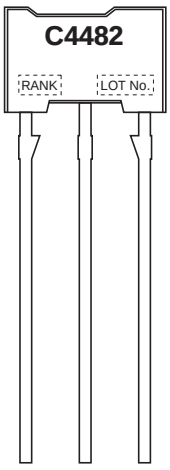
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions
unit : mm (typ)
7540-001

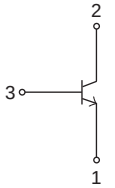


Product & Package Information
- Package : NMP(Taping)
- JEITA, JEDEC : SC-71
- Minimum Packing Quantity : 2,500 pcs./box

Marking(NMP(Taping))



Electrical Connection



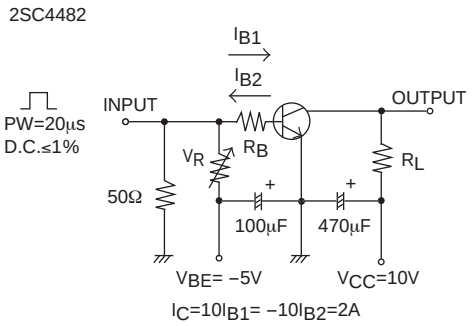
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=50V, I_E=0A			100	nA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0A			100	nA
DC Current Gain	$h_{FE}1$	V_{CE}=2V, I_C=500mA	200*		560*	
	$h_{FE}2$	V_{CE}=2V, I_C=3A	95			
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=50mA		150		MHz
Output Capacitance	Cob	V_{CB}=10V, f=1MHz		45		pF
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)	I_C=3A, I_B=60mA		220	500	mV
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=3A, I_B=60mA			1.5	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0A	60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	20			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0A	6			V
Turn-ON Time	t_{on}	See specified Test Circuit.		30		ns
Storage Time	t_{stg}			300		ns
Fall Time	t_f			40		ns

* : The 2SC4482 is classified by 500mA h_{FE} as follows :

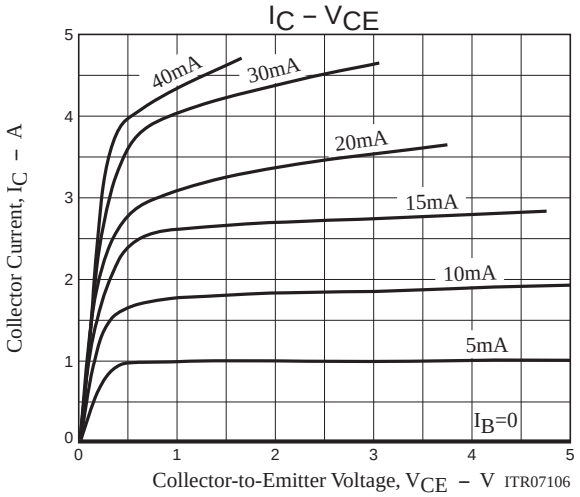
Rank	T	U
h_{FE}	200 to 400	280 to 560

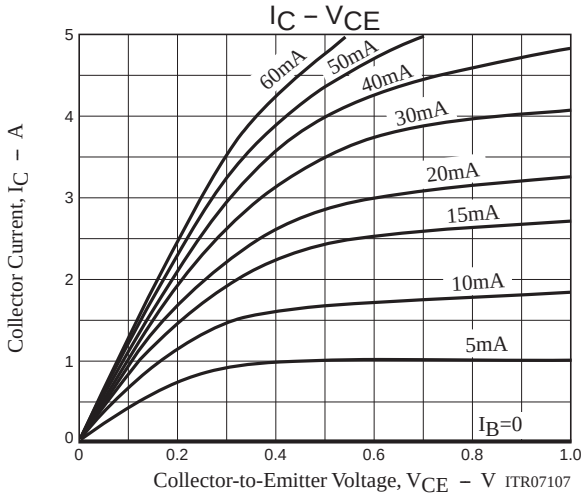
Switching Time Test Circuit

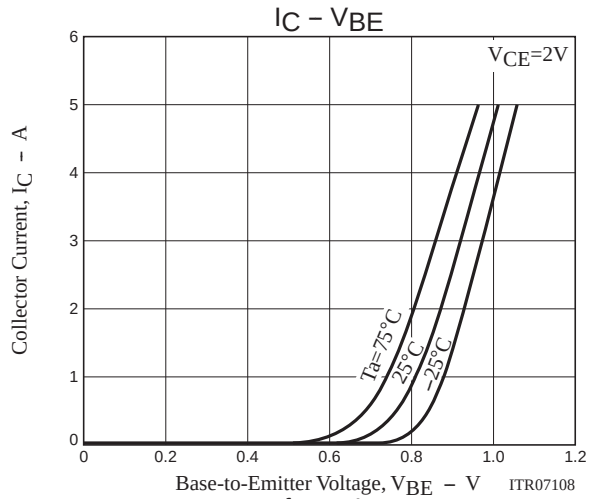


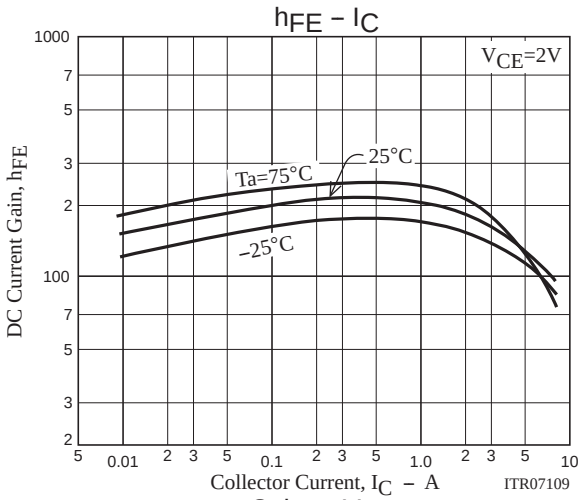
Ordering Information

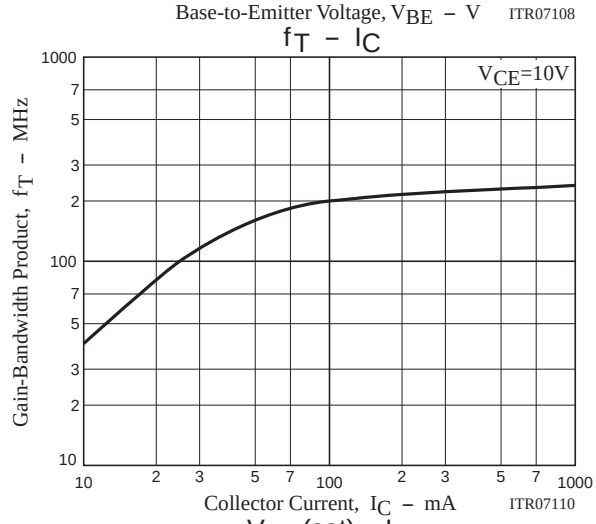
Device	Package	Shipping	memo
2SC4482T-AN	NMP(Taping)	2,500pcs./box	Pb Free
2SC4482U-AN	NMP(Taping)	2,500pcs./box	

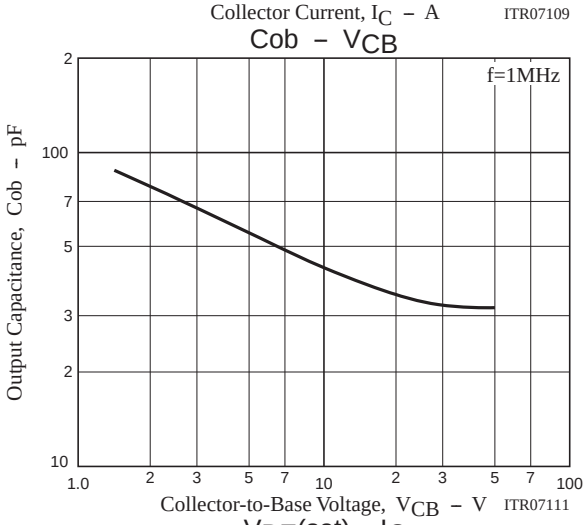


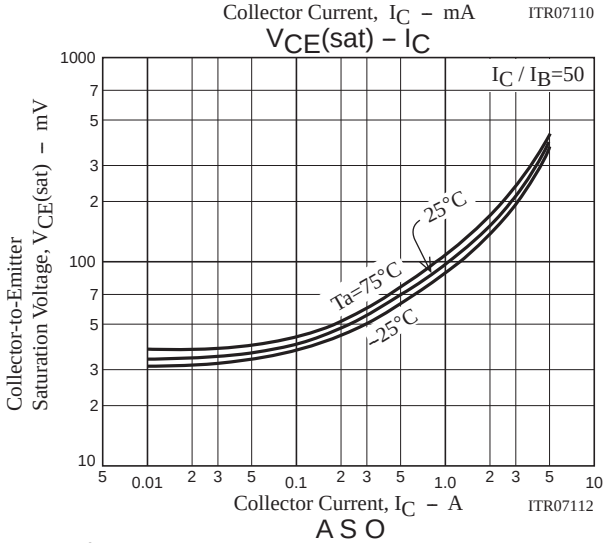


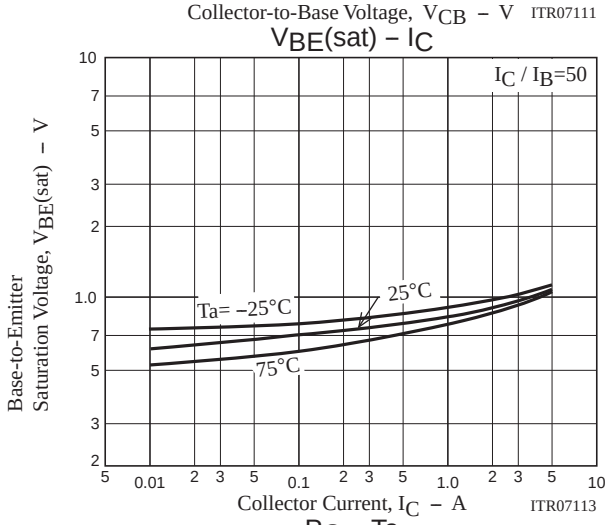

IC – VBE
VCE=2V
Collector Current, IC – A
Base-to-Emitter Voltage, VBE – V
Ta=75°C
25°C
–25°C
ITR07108

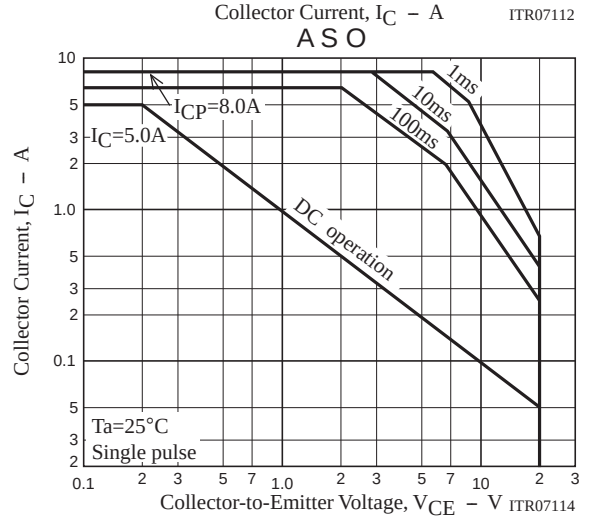

hFE – IC
VCE=2V
DC Current Gain, hFE
Collector Current, IC – A
Ta=75°C
25°C
–25°C
ITR07109

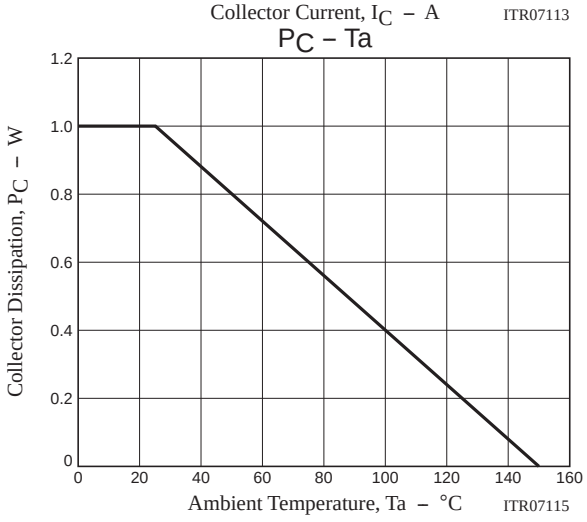

fT – IC
VCE=10V
Gain-Bandwidth Product, fT – MHz
Collector Current, IC – mA
ITR07110


Cob – VCB
f=1MHz
Output Capacitance, Cob – pF
Collector-to-Base Voltage, VCB – V
ITR07111


VCE(sat) – IC
IC / IB=50
Collector-to-Emitter Saturation Voltage, VCE(sat) – mV
Collector Current, IC – A
Ta=75°C
25°C
–25°C
ITR07112


VBE(sat) – IC
IC / IB=50
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A
Ta= –25°C
25°C
75°C
ITR07113


A S O
ICP=8.0A
IC=5.0A
1ms
10ms
100ms
DC operation
Ta=25°C
Single pulse
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V
ITR07114


PC – Ta
Collector Dissipation, PC – W
Ambient Temperature, Ta – °C
ITR07115

Bag Packing Specification

2SC4482T-AN, 2SC4482U-AN

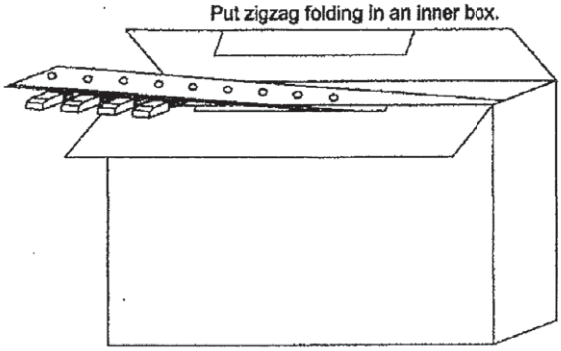
NMP (Zigzag folding)

Storage package Outline name	Package type	Maximum Number of devices contained (pcs.)		Packing format	
		Inner box No.	Storage quantity	Outer box (C—6)	Outer box (C—8)
NMP	AN/AZ	C—3 Inner box Dimensions :mm(external) 330×45×125	2,500	8 inner boxes contained(20,000pcs.) Outer box Dimensions:mm(external) 585×345×195	4 inner boxes contained(10,000pcs.) Outer box Dimensions:mm(external) 345×300×195

1. Packing format

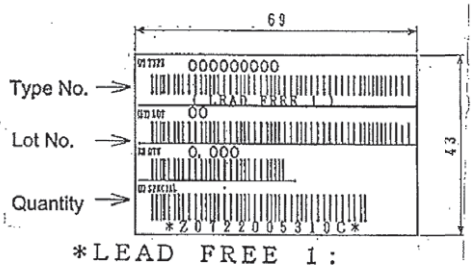
Packing method

Put zigzag folding in an inner box.



2. Bar code label

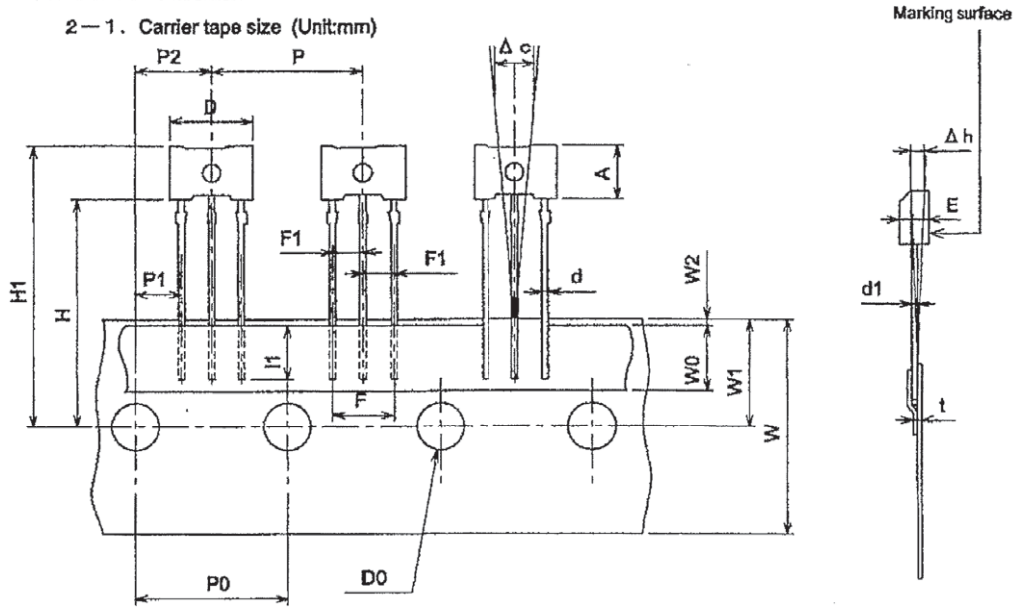
(Unit : mm)



*LEAD FREE 1:
Lead-free External terminal surface treatment product.

2. Taping specifications

2—1. Carrier tape size (Unit:mm)



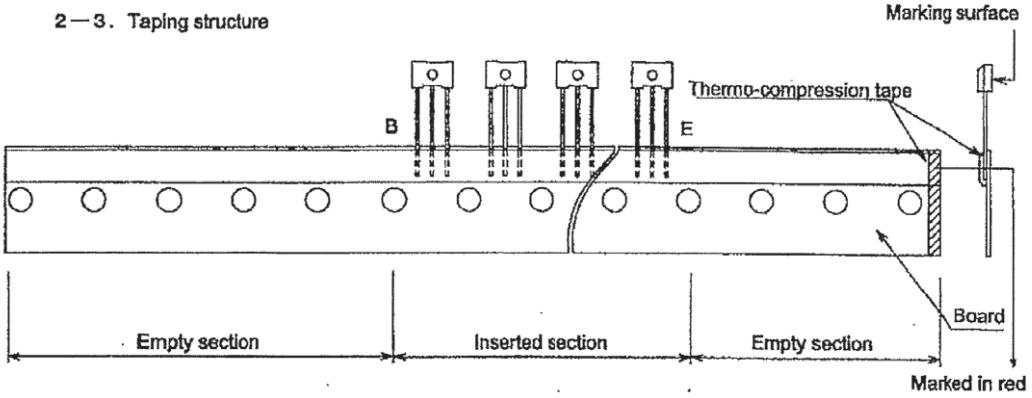
2—2. Taping size standard

Unit:mm

Item	Symbol	Standard	Tolerance
Work piece outside diameter	D	6.9	±0.2
	E	2.5	±0.2
Work piece height	A	4.5	±0.2
Lead wire diameter	d	0.5	±0.1
Lead wire thickness	d1	0.45	±0.1
Bonded lead wire	l1	3.0MIN	
Pitch between products	P	12.7	±0.5
Pitch between perforations	P0	12.7	±0.2
Total pitch for 21 perforations	P0×20	254.0	±1.0
Distance between lead wire	F	5.0	+0.8 -0.2
Lead wire pitch distance	F1	2.54	+0.4 -0.1
Displacement of perforations	P1	3.81	±0.3
	P2	6.35	±0.3
Displacement of tape	W2	0～0.5	

Item	Symbol	Standard	Tolerance
Tape width	W	18.0	±0.5
Adhesive tape	W0	6.0	±0.5
Displacement of perforations	W1	9.0	±0.5
Work piece bottom surface position	H	19.0	+1.0 -0.5
Work piece upper limit position	H1	23.5	±1.0
Perforations diameter	D0	φ4.0	±0.2
Tape thickness (total thickness)	t	0.6	±0.2
Product inclination	Δc	0	±0.7
Product inclination	Δh	0	±1.0

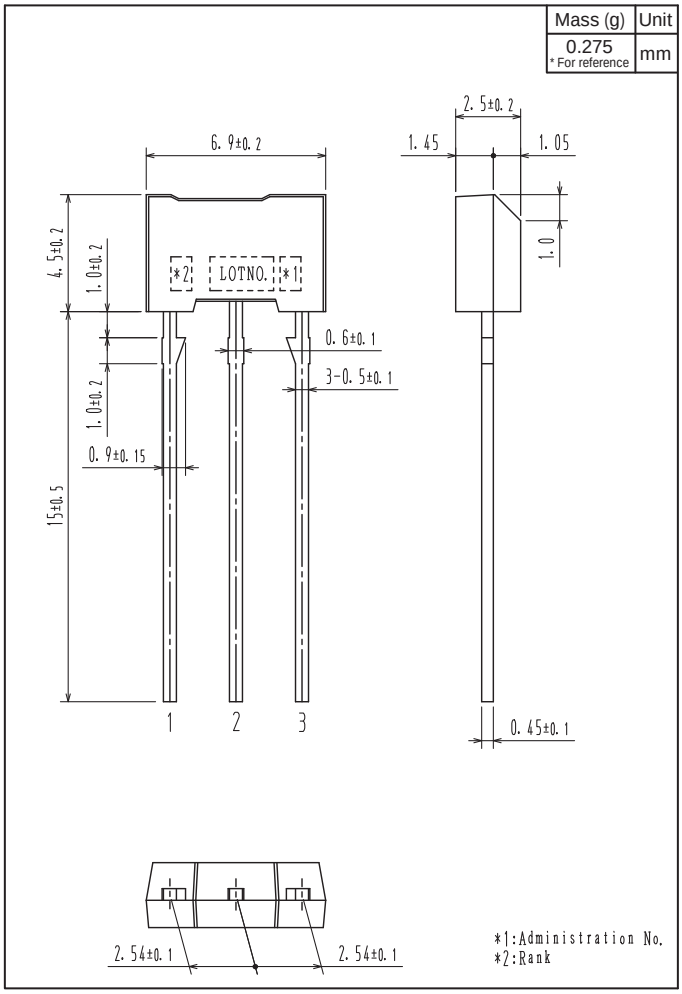
2—3. Taping structure



- Provide an empty section for about three to five pieces in leading and end portions of the tape.
- Provide an empty section in the fold-back portion.
- Provide marking in red to the E-side end of the board.

Outline Drawing

2SC4482T-AN, 2SC4482U-AN



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